Title (en)

METHOD FOR PRODUCING A THIN LAYER PHOTOVOLTAIC SYSTEM AND THIN LAYER PHOTOVOLTAIC SYSTEM

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES DÜNNSCHICHT-PHOTOVOLTAIK-SYSTEMS UND DÜNNSCHICHT-PHOTOVOLTAIK-SYSTEM

Title (fr)

PROCÉDÉ DE FABRICATION D'UN SYSTÈME PHOTOVOLTAÏQUE EN COUCHES MINCES ET SYSTÈME PHOTOVOLTAÏQUE EN COUCHES MINCES

Publication

EP 2404326 A2 20120111 (DE)

Application

EP 10702684 A 20100205

Priority

- EP 2010051406 W 20100205
- DE 102009007908 A 20090206

Abstract (en)

[origin: EP2216832A2] The method involves using a flat metal chalcogenide compound semiconductor layer as an absorber for sunlight and a metal layer applied to the metal chalcogenide compound semiconductor layer. The metal chalcogenide compound semiconductor layer and the metal layer form a Schottky contact at their contact surface. The metal chalcogenide compound semiconductor layer is manufactured by applying a dispersion containing nano-scale particles with a diameter of about 3 to 30 nanometer on a transparent substrate material.

IPC 8 full level

H01L 31/032 (2006.01); **H01L 27/142** (2006.01); **H01L 31/0392** (2006.01); **H01L 31/048** (2006.01); **H01L 31/07** (2012.01); **H01L 31/18** (2006.01)

CPC (source: EP US)

B32B 17/10018 (2013.01 - EP US); **B32B 17/10761** (2013.01 - EP US); **B32B 17/10788** (2013.01 - EP US); **H01L 31/0296** (2013.01 - EP US); **H01L 31/032** (2013.01 - EP US); **H01L 31/0392** (2013.01 - EP US); **H01L 31/03925** (2013.01 - EP US); **H01L 31/07** (2013.01 - EP US); **H01L 31/1836** (2013.01 - EP US); B32B 2327/12 (2013.01 - EP US); H01L 21/02551 (2013.01 - EP US); H01L 21/02568 (2013.01 - EP US); H01L 21/02601 (2013.01 - EP US); H01L 21/02628 (2013.01 - EP US); Y02E 10/50 (2013.01 - EP US)

Citation (search report)

See references of WO 2010089364A2

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DOCDB simple family (application)

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